LM4040/LM4041

Precision Micropower Shunt Voltage Reference

Features

- Small SOT-23 Package
- No Output Capacitor Required
- Tolerates Capacitive Loads
- Fixed Reverse-Breakdown Voltages of 1.225V, 2.500V, 4.096V, and 5.000V
- Adjustable Reverse-Breakdown Version

Applications

- Battery-Powered Equipment
- Data Acquisition Systems
- Instrumentation
- Process Control
- Energy Management
- Product Testing
- Automotive Electronics
- Precision Audio Components

General Description

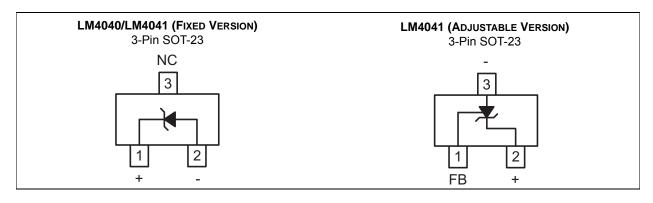
Ideal for space critical applications, the LM4040 and LM4041 precision voltage references are available in the subminiature SOT-23 surface-mount package.

The LM4040 is available in fixed reverse-breakdown voltages of 2.500V, 4.096V, and 5.000V. The LM4041 is available with a fixed 1.225V or an adjustable reverse-breakdown voltage.

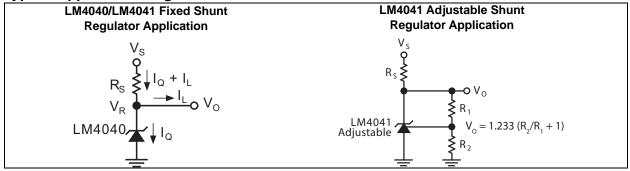
The minimum operating current ranges from 60 μ A for the LM4041-1.2 to 74 μ A for the LM4040-5.0. LM4040 versions have a maximum operating current of 15 mA. LM4041 versions have a maximum operating current of 12 mA.

The LM4040 and LM4041 have bandgap reference temperature drift curvature correction and low dynamic impedance, ensuring stable reverse-breakdown voltage accuracy over a wide range of operating temperatures and currents.

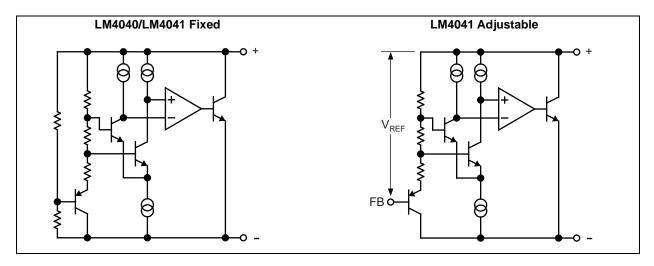
Package Types



Typical Application Diagrams



Functional Block Diagrams



1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings †

Reverse Current	
Forward Current	
Maximum Output Voltage (LM4041-ADJ)	
Power Dissipation ($T_A = +25^{\circ}C$; Note 1).	
ESD Susceptibility (HBM; Note 2)	
ESD Susceptibility (MM; Note 2)	

Operating Ratings ‡

Reverse Current (LM4040-2.5)	60 µA to 15 mA
Reverse Current (LM4040-4.1)	
Reverse Current (LM4040-5.0)	
Reverse Current (LM4041-1.2)	-
Reverse Current (LM4041-ADJ)	•
Output Voltage Range (LM4041-ADJ)	•

† Notice: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

‡ Notice: The device is not guaranteed to function outside its operating ratings.

- **Note 1:** The maximum power dissipation must be derated at elevated temperatures and is dictated by T_{JMAX} (maximum junction temperature), Θ_{JA} (junction-to-ambient thermal resistance), and T_A (ambient temperature). The maximum allowable power dissipation at any temperature is $P_{DMAX} = (T_{JMAX} T_A)/\Theta_{JA}$ or the number given in the Absolute Maximum Ratings, whichever is lower. For the LM4040 and LM4041, $T_{JMAX} = +125^{\circ}C$ and the typical thermal resistance, when board-mounted, is +326°C/W for the SOT-23 package.
 - **2:** Devices are ESD sensitive. Handling precautions are recommended. Human body model, $1.5 \text{ k}\Omega$ in series with 100 pF. The machine model is a 200 pF capacitor discharged directly into each pin.

LM4040-2.5 ELECTRICAL CHARACTERISTICS (Note 1)

 T_A = Operating Temperature Range, $T_A = T_J = -40^{\circ}C$ to +85°C, unless noted.

Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions
LM4040C						
Reverse-Breakdown Voltage	V _R	_	2.500	_	V	I _R = 100 μA, T _A = +25°C
Reverse-Breakdown Voltage		_	_	±12	mV	I _R = 100 μA, T _A = +25°C
Tolerance (Note 2)		_	_	±29	mV	I _R = 100 μΑ
Minimum Operating Current	I _{RMIN}	_	45	60	μA	T _A = +25°C
		_	_	65		_
Average Reverse-Breakdown	$\Delta V_R / \Delta_T$	_	±20	_	ppm/°C	I _R = 10 mA, T _A = +25°C
Voltage Temperature Coefficient		_	±15	±100		I _R = 1 mA
Coemcient		_	±15	_		I _R = 100 μA, T _A = +25°C
Reverse-Breakdown Voltage Change with Operating	$\Delta V_R / \Delta I_R$	_	0.3	0.8	mV	I _{RMIN} ≤ I _R ≤ 1 mA, T _A = +25°C
Current Change		_	_	1.0		I _{RMIN} ≤ I _R ≤ 1 mA
		_	2.5	6.0		1 mA ≤ I _R ≤ 15 mA, T _A = +25°C
		_	_	8.0		1 mA ≤ I _R ≤ 15 mA
Reverse Dynamic Impedance	Z _R	—	0.3	0.9	Ω	I _R = 1 mA, f = 120 Hz, I _{AC} = 0.1 I _R , T _A = +25°C
Wideband Noise	e _N	_	35	_	μV _{RMS}	I _R = 100 μA, T _A = +25°C, 10 Hz ≤ f ≤ 10 kHz
Reverse-Breakdown Voltage Long-Term Stability	ΔV_R	_	120	_	ppm	t = 1000 hrs., T _A = +25°C ±0.1°C, I _R = 100 μA
LM4040D						
Reverse-Breakdown Voltage	V _R	_	2.500	_	V	I _R = 100 μA, T _A = +25°C
Reverse-Breakdown Voltage				±25	mV	I _R = 100 μA, T _A = +25°C
Tolerance (Note 2)		_	_	±49	mV	I _R = 100 μA
Minimum Operating Current	I _{RMIN}	_	45	65	μA	T _A = +25°C
		_	_	70		_
Average Reverse-Breakdown	$\Delta V_R / \Delta_T$		±20		ppm/°C	I _R = 10 mA, T _A = +25°C
Voltage Temperature Coefficient		_	±15	±150		I _R = 1 mA
Cochloicht			±15			I _R = 100 μA, T _A = +25°C

Note 1: Specification for packaged product only.

b. D-grade: ±1.98% = ±1.0% ±150 ppm/°C × 65°C

^{2:} The boldface (overtemperature) limit for Reverse-Breakdown Voltage Tolerance is defined as the room temperature Reverse-Breakdown Voltage Tolerance ±[(ΔV_R/ΔT)(65°C)(V_R)]. ΔV_R/ΔT is the V_R temperature coefficient, 65°C is the temperature range from -40°C to the reference point of 25°C, and V_R is the reverse-breakdown voltage. The total overtemperature tolerance for the different grades follows: a. C-grade: ±1.15% = ±0.5% ±100 ppm/°C × 65°C

LM4040-2.5 ELECTRICAL CHARACTERISTICS (Note 1) (CONTINUED)

T _A = Operating Temperature Ra	ange. T∧ = T⊥ = -40°	C to +85°C, unless noted.
A operating temperature ta	•	

Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions
Reverse-Breakdown Voltage Change with Operating	$\Delta V_R / \Delta I_R$	_	0.3	1.0	mV	$I_{RMIN} \le I_R \le 1 \text{ mA},$ $T_A = +25^{\circ}\text{C}$
Current Change		_		1.2		I _{RMIN} ≤ I _R ≤ 1 mA
			2.5	8.0		1 mA ≤ I _R ≤ 15 mA, T _A = +25°C
			_	10.0		1 mA ≤ I _R ≤ 15 mA
Reverse Dynamic Impedance	Z _R	—	0.3	1.1	Ω	I _R = 1 mA, f = 120 Hz, I _{AC} = 0.1 I _R , T _A = +25°C
Wideband Noise	e _N	—	35	—	μV _{RMS}	I _R = 100 μA, 10 Hz ≤ f ≤ 10 kHz
Reverse-Breakdown Voltage Long-Term Stability	ΔV_R	_	120	_	ppm	t = 1000 hrs., T _A = +25°C ±0.1°C, I _R = 100 μA

Note 1: Specification for packaged product only.

2: The boldface (overtemperature) limit for Reverse-Breakdown Voltage Tolerance is defined as the room temperature Reverse-Breakdown Voltage Tolerance ±[(ΔV_R/ΔT)(65°C)(V_R)]. ΔV_R/ΔT is the V_R temperature coefficient, 65°C is the temperature range from -40°C to the reference point of 25°C, and V_R is the reverse-breakdown voltage. The total overtemperature tolerance for the different grades follows:

a. C-grade: ±1.15% = ±0.5% ±100 ppm/°C × 65°C

b. D-grade: ±1.98% = ±1.0% ±150 ppm/°C × 65°C

LM4040-4.1 ELECTRICAL CHARACTERISTICS (Note 1)

 T_A = Operating Temperature Range, $T_A = T_J = -40^{\circ}C$ to +85°C, unless noted.

Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions
LM4040C			•			
Reverse-Breakdown Voltage	V _R	_	4.096	—	V	I _R = 100 μA, T _A = +25°C
Reverse-Breakdown Voltage		_	_	±20	mV	I _R = 100 μA, T _A = +25°C
Tolerance (Note 2)		_	_	±47	mV	I _R = 100 μA
Minimum Operating Current	I _{RMIN}	_	50	68	μA	T _A = +25°C
		_	_	73		_
Average Reverse-Breakdown	$\Delta V_R / \Delta_T$	_	±30	_	ppm/°C	I _R = 10 mA, T _A = +25°C
Voltage Temperature Coefficient		_	±20	±100]	I _R = 1 mA
Coemcient		_	±20	_]	I _R = 100 μA, T _A = +25°C
Reverse-Breakdown Voltage Change with Operating	$\Delta V_R / \Delta I_R$	_	0.5	0.9	mV	I _{RMIN} ≤ I _R ≤ 1 mA, T _A = +25°C
Current Change		_	_	1.2		I _{RMIN} ≤ I _R ≤ 1 mA
		_	3.0	7.0		1 mA ≤ I _R ≤ 15 mA, T _A = +25°C
		_	—	10.0		1 mA ≤ I _R ≤ 15 mA
Reverse Dynamic Impedance	Z _R	—	0.5	1.0	Ω	I _R = 1 mA, f = 120 Hz, I _{AC} = 0.1 I _R , T _A = +25°C
Wideband Noise	e _N	_	80	_	μV _{RMS}	I _R = 100 μA, T _A = +25°C, 10 Hz ≤ f ≤ 10 kHz
Reverse-Breakdown Voltage Long-Term Stability	ΔV_R	_	120	_	ppm	t = 1000 hrs., T _A = +25°C ±0.1°C, I _R = 100 μA
LM4040D			-			
Reverse-Breakdown Voltage	V _R	_	4.096	_	V	I _R = 100 μA, T _A = +25°C
Reverse-Breakdown Voltage	Ē			±41	mV	I _R = 100 μA, T _A = +25°C
Tolerance (Note 2)			_	±81	mV	I _R = 100 μA
Minimum Operating Current	I _{RMIN}	_	50	73	μA	T _A = +25°C
				78		_
Average Reverse-Breakdown	$\Delta V_R / \Delta_T$	_	±30	_	ppm/°C	I _R = 10 mA, T _A = +25°C
Voltage Temperature Coefficient	Γ		±20	±150]	I _R = 1 mA
COCINCICIIL	Ē		±20			I _R = 100 μA, T _A = +25°C

Note 1: Specification for packaged product only.

b. D-grade: ±1.98% = ±1.0% ±150 ppm/°C × 65°C

 ^{2:} The boldface (overtemperature) limit for Reverse-Breakdown Voltage Tolerance is defined as the room temperature Reverse-Breakdown Voltage Tolerance ±[(ΔV_R/ΔT)(65°C)(V_R)]. ΔV_R/ΔT is the V_R temperature coefficient, 65°C is the temperature range from -40°C to the reference point of 25°C, and V_R is the reverse-breakdown voltage. The total overtemperature tolerance for the different grades follows:

 a. C-grade: ±1.15% = ±0.5% ±100 ppm/°C × 65°C

LM4040-4.1 ELECTRICAL CHARACTERISTICS (Note 1) (CONTINUED)

T_A = Operating Temperature Range, T_A = T_J = -40°C to +85°C, unless noted.	T_{Δ} = Operating Temperatur	re Range, T _A = T ₁ =	= –40°C to +85°C, unless noted.
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Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions
Reverse-Breakdown Voltage Change with Operating	$\Delta V_R / \Delta I_R$	_	0.5	1.2	mV	$I_{RMIN} \le I_R \le 1 \text{ mA},$ $T_A = +25^{\circ}\text{C}$
Current Change				1.5		I _{RMIN} ≤ I _R ≤ 1 mA
		—	3.0	9.0		1 mA ≤ I _R ≤ 15 mA, T _A = +25°C
		_	_	13.0		1 mA ≤ I _R ≤ 15 mA
Reverse Dynamic Impedance	Z _R	—	0.5	1.3	Ω	I _R = 1 mA, f = 120 Hz, I _{AC} = 0.1 I _R , T _A = +25°C
Wideband Noise	e _N	_	80	_	μV _{RMS}	I _R = 100 µA, T _A = +25°C 10 Hz ≤ f ≤ 10 kHz
Reverse-Breakdown Voltage Long-Term Stability	ΔV_R	_	120	_	ppm	t = 1000 hrs., T _A = +25°C ±0.1°C, I _R = 100 μA

Note 1: Specification for packaged product only.

2: The boldface (overtemperature) limit for Reverse-Breakdown Voltage Tolerance is defined as the room temperature Reverse-Breakdown Voltage Tolerance ±[(ΔV_R/ΔT)(65°C)(V_R)]. ΔV_R/ΔT is the V_R temperature coefficient, 65°C is the temperature range from -40°C to the reference point of 25°C, and V_R is the reverse-breakdown voltage. The total overtemperature tolerance for the different grades follows:

a. C-grade: ±1.15% = ±0.5% ±100 ppm/°C × 65°C

b. D-grade: ±1.98% = ±1.0% ±150 ppm/°C × 65°C

LM4040-5.0 ELECTRICAL CHARACTERISTICS (Note 1)

 T_A = Operating Temperature Range, $T_A = T_J = -40^{\circ}C$ to +85°C, unless noted.

Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions
LM4040C						
Reverse-Breakdown Voltage	V _R		5.000	_	V	I _R = 100 μA, T _A = +25°C
Reverse-Breakdown Voltage		_	_	±25	mV	I _R = 100 μA, T _A = +25°C
Tolerance (Note 2)		_	_	±58	mV	I _R = 100 μA
Minimum Operating Current	I _{RMIN}		54	74	μA	T _A = +25°C
		_	_	80		_
Average Reverse-Breakdown	$\Delta V_R / \Delta_T$		±30	_	ppm/°C	I _R = 10 mA, T _A = +25°C
Voltage Temperature Coefficient			±20	±100		I _R = 1 mA
COEMORENI		_	±20	_		I _R = 100 μA, T _A = +25°C
Reverse-Breakdown Voltage Change with Operating	$\Delta V_R / \Delta I_R$	_	0.5	1.0	mV	I _{RMIN} ≤ I _R ≤ 1 mA, T _A = +25°C
Current Change		_	—	1.4		I _{RMIN} ≤ I _R ≤ 1 mA
		_	3.5	8.0		1 mA ≤ I _R ≤ 15 mA, T _A = +25°C
			_	12.0		1 mA ≤ I _R ≤ 15 mA
Reverse Dynamic Impedance	Z _R	—	0.5	1.1	Ω	I _R = 1 mA, f = 120 Hz, I _{AC} = 0.1 I _R , T _A = +25°C
Wideband Noise	e _N	_	80	_	μV _{RMS}	I _R = 100 μA, T _A = +25°C, 10 Hz ≤ f ≤ 10 kHz
Reverse-Breakdown Voltage Long-Term Stability	ΔV_R	_	120	_	ppm	t = 1000 hrs., T _A = +25°C ±0.1°C, I _R = 100 μA
LM4040D						
Reverse-Breakdown Voltage	V _R	_	5.000	_	V	I _R = 100 μA, T _A = +25°C
Reverse-Breakdown Voltage				±50	mV	I _R = 100 μA, T _A = +25°C
Tolerance (Note 2)			_	±99	mV	I _R = 100 μA
Minimum Operating Current	I _{RMIN}		54	79	μΑ	T _A = +25°C
			_	85		_
Average Reverse-Breakdown	$\Delta V_R / \Delta_T$	_	±30	_	ppm/°C	I _R = 10 mA, T _A = +25°C
Voltage Temperature Coefficient			±20	±150		I _R = 1 mA
			±20	_]	I _R = 100 μA, T _A = +25°C

Note 1: Specification for packaged product only.

b. D-grade: ±1.98% = ±1.0% ±150 ppm/°C × 65°C

 ^{2:} The boldface (overtemperature) limit for Reverse-Breakdown Voltage Tolerance is defined as the room temperature Reverse-Breakdown Voltage Tolerance ±[(ΔV_R/ΔT)(65°C)(V_R)]. ΔV_R/ΔT is the V_R temperature coefficient, 65°C is the temperature range from -40°C to the reference point of 25°C, and V_R is the reverse-breakdown voltage. The total overtemperature tolerance for the different grades follows:

 a. C-grade: ±1.15% = ±0.5% ±100 ppm/°C × 65°C

LM4040-5.0 ELECTRICAL CHARACTERISTICS (Note 1) (CONTINUED)

T - Operating	Tomporatura Dana	<u>ат – т</u>	$= 40^{\circ}$ C to $\pm 95^{\circ}$ C unloss noted
	Temperature Range	Ξ, ΙΔ - Ι	$_{\rm J}$ = -40°C to +85°C, unless noted.

Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions
Reverse-Breakdown Voltage Change with Operating	$\Delta V_R / \Delta I_R$	_	0.5	1.3	mV	I _{RMIN} ≤ I _R ≤ 1 mA, T _A = +25°C
Current Change			_	1.8		I _{RMIN} ≤ I _R ≤ 1 mA
		—	3.5	10.0		1 mA ≤ I _R ≤ 15 mA, T _A = +25°C
			_	15.0		1 mA ≤ I _R ≤ 15 mA
Reverse Dynamic Impedance	Z _R	—	0.5	1.5	Ω	I _R = 1 mA, f = 120 Hz, I _{AC} = 0.1 I _R , T _A = +25°C
Wideband Noise	e _N	—	80	_	μV _{RMS}	I _R = 100 μA, T _A = +25°C, 10 Hz ≤ f ≤ 10 kHz
Reverse-Breakdown Voltage Long-Term Stability	ΔV_R	_	120	—	ppm	t = 1000 hrs., T _A = +25°C ±0.1°C, I _R = 100 μA

Note 1: Specification for packaged product only.

2: The boldface (overtemperature) limit for Reverse-Breakdown Voltage Tolerance is defined as the room temperature Reverse-Breakdown Voltage Tolerance ±[(ΔV_R/ΔT)(65°C)(V_R)]. ΔV_R/ΔT is the V_R temperature coefficient, 65°C is the temperature range from -40°C to the reference point of 25°C, and V_R is the reverse-breakdown voltage. The total overtemperature tolerance for the different grades follows:

a. C-grade: ±1.15% = ±0.5% ±100 ppm/°C × 65°C

b. D-grade: ±1.98% = ±1.0% ±150 ppm/°C × 65°C

LM4041-1.2 ELECTRICAL CHARACTERISTICS (Note 1)

 T_A = Operating Temperature Range, $T_A = T_J = -40^{\circ}$ C to +85°C, unless noted.

Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions
LM4041C	· · ·		•		•	·
Reverse-Breakdown Voltage	V _R	_	1.225	_	V	I _R = 100 μA, T _A = +25°C
Reverse-Breakdown Voltage		_	_	±6	mV	I _R = 100 μA, T _A = +25°C
Tolerance (Note 2)		_	_	±14	mV	I _R = 100 μA
Minimum Operating Current	I _{RMIN}	_	45	60	μA	T _A = +25°C
		_	_	65		_
Average Reverse-Breakdown	$\Delta V_R / \Delta_T$	_	±20	_	ppm/°C	I _R = 10 mA, T _A = +25°C
Voltage Temperature Coefficient		_	±15	±100		I _R = 1 mA
Coemcient		_	±15	_		I _R = 100 μA, T _A = +25°C
Reverse-Breakdown Voltage Change with Operating	$\Delta V_R / \Delta I_R$	_	0.7	1.5	mV	I _{RMIN} ≤ I _R ≤ 1 mA, T _A = +25°C
Current Change		_	—	2.0		I _{RMIN} ≤ I _R ≤ 1 mA
		_	4.0	6.0		1 mA ≤ I _R ≤ 12 mA, T _A = +25°C
		_	—	8.0		1 mA ≤ I _R ≤ 12 mA
Reverse Dynamic Impedance	Z _R	—	0.5	1.5	Ω	I _R = 1 mA, f = 120 Hz, I _{AC} = 0.1 I _R , T _A = +25°C
Wideband Noise	e _N	_	20	_	μV _{RMS}	I _R = 100 μA, T _A = +25°C, 10 Hz ≤ f ≤ 10 kHz
Reverse-Breakdown Voltage Long-Term Stability	ΔV _R	_	120	_	ppm	t = 1000 hrs., T _A = +25°C ±0.1°C, I _R = 100 μA
LM4041D			-		•	
Reverse-Breakdown Voltage	V _R	_	1.225	_	V	I _R = 100 μA, T _A = +25°C
Reverse-Breakdown Voltage		_	_	±12	mV	I _R = 100 μA, T _A = +25°C
Tolerance (Note 2)				±24		I _R = 100 μA
Minimum Operating Current	I _{RMIN}	_	45	65	μA	T _A = +25°C
		_	_	70	1	_
Average Reverse-Breakdown	$\Delta V_R / \Delta_T$	_	±20	_	ppm/°C	I _R = 10 mA, T _A = +25°C
Voltage Temperature Coefficient		_	±15	±150		I _R = 1 mA
COEIIICICIII		_	±15	_	1	I _R = 100 μA, T _A = +25°C

Note 1: Specification for packaged product only.

b. D-grade: ±1.98% = ±1.0% ±150 ppm/°C × 65°C

^{2:} The boldface (overtemperature) limit for Reverse-Breakdown Voltage Tolerance is defined as the room temperature Reverse-Breakdown Voltage Tolerance ±[(ΔV_R/ΔT)(65°C)(V_R)]. ΔV_R/ΔT is the V_R temperature coefficient, 65°C is the temperature range from -40°C to the reference point of 25°C, and V_R is the reverse-breakdown voltage. The total overtemperature tolerance for the different grades follows: a. C-grade: ±1.15% = ±0.5% ±100 ppm/°C × 65°C

LM4041-1.2 ELECTRICAL CHARACTERISTICS (Note 1) (CONTINUED)

$T_{\Delta} = Operating Temperature Range, T_{\Delta} = T_{\perp} = -40 \text{ G to +65 G, unless noted.}$	T_A = Operating Temperature Range, T_A = T_J = -40°C to +85	°C, unless noted.
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Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions		
Reverse-Breakdown Voltage Change with Operating	$\Delta V_R / \Delta I_R$	_	0.7	2.0	mV	$I_{RMIN} \le I_R \le 1 \text{ mA},$ $T_A = +25^{\circ}\text{C}$		
Current Change				2.5		I _{RMIN} ≤ I _R ≤ 1 mA		
		_	2.5	8.0		1 mA ≤ I _R ≤ 12 mA, T _A = +25°C		
				10.0		1 mA ≤ I _R ≤ 12 mA		
Reverse Dynamic Impedance	Z _R	_	0.5	2.0	Ω	I _R = 1 mA, f = 120 Hz, I _{AC} = 0.1 I _R , T _A = +25°C		
Wideband Noise	e _N	_	20	_	μV _{RMS}	I _R = 100 μA, T _A = +25°C, 10 Hz ≤ f ≤ 10 kHz		
Reverse-Breakdown Voltage Long-Term Stability	ΔV_R		120	_	ppm	t = 1000 hrs., T _A = +25°C ±0.1°C, I _R = 100 μA		

Note 1: Specification for packaged product only.

2: The boldface (overtemperature) limit for Reverse-Breakdown Voltage Tolerance is defined as the room temperature Reverse-Breakdown Voltage Tolerance ±[(ΔV_R/ΔT)(65°C)(V_R)]. ΔV_R/ΔT is the V_R temperature coefficient, 65°C is the temperature range from -40°C to the reference point of 25°C, and V_R is the reverse-breakdown voltage. The total overtemperature tolerance for the different grades follows:

a. C-grade: ±1.15% = ±0.5% ±100 ppm/°C × 65°C

b. D-grade: ±1.98% = ±1.0% ±150 ppm/°C × 65°C

LM4041-ADJ ELECTRICAL CHARACTERISTICS (Note 1)

 T_A = Operating Temperature Range, $T_A = T_J = -40^{\circ}C$ to +85°C, unless noted.

Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions
LM4041C						
Reverse-Breakdown Voltage	V _R		1.233		V	I _R = 100 μA, V _{OUT} = 5V
Reverse-Breakdown Voltage		_	—	±6.2	mV	I _R = 100 μA, T _A = +25°C
Tolerance (Note 2)		_	—	±14	mV	I _R = 100 μA
Minimum Operating Current	I _{RMIN}		45	60	μA	T _A = +25°C
				65		—
Reference Voltage Change with Operating Current	$\Delta V_{REF} / \Delta I_R$	_	0.7	1.5	mV	I _{RMIN} ≤ I _R ≤ 1 mA, V _{OUT} ≥ 1.6V (Note 3), T _A = +25°C
		—	—	2.0		I _{RMIN} ≤ I _R ≤ 1 mA, V _{OUT} ≥ 1.6V (Note 3)
		_	2.0	4.0		1 mA ≤ I _R ≤ 12 mA, V _{OUT} ≥ 1.6V (Note 3), T _A = +25°C
		—	—	6.0		1 mA ≤ I _R ≤ 12 mA, V _{OUT} ≥ 1.6V (Note 3)
Reference Voltage Change	$\Delta V_{REF} / \Delta V_O$	_	-1.55	-2.0	mV/V	I _R = 1 mA, T _A = +25°C
with Output Voltage Change		_	—	-2.5		I _R = 1 mA
Feedback Current	I _{FB}	_	60	100	nA	T _A = +25°C
				120		—
Average Reference Voltage Temperature Coefficient	ΔV _{REF} / ΔT	_	±20		ppm/°C	V _{OUT} = 5V, I _R = 10 mA, T _A = +25°C
			±15	±100		V _{OUT} = 5V, I _R = 1 mA
		—	±15	_		V _{OUT} = 5V, I _R = 100 μA, T _A = +25°C
Dynamic Output Impedance	Z _{OUT}	_	0.3	_	Ω	I _R = 1 mA, f = 120 Hz, T _A = +25°C, I _{AC} = 0.1 I _R , V _{OUT} = V _{REF}
				2.0		V _{OUT} = 10V, T _A = +25°C
Wideband Noise	e _N	_	20	_	μV _{RMS}	I _R = 100 μA, T _A = +25°C, 10 Hz ≤ f ≤ 10 kHz

Note 1: Specification for packaged product only.

- **2:** The boldface (overtemperature) limit for Reverse-Breakdown Voltage Tolerance is defined as the room temperature Reverse-Breakdown Voltage Tolerance $\pm [(\Delta V_R/\Delta T)(65^\circ C)(V_R)]$. $\Delta V_R/\Delta T$ is the V_R temperature coefficient, 65°C is the temperature range from -40°C to the reference point of 25°C, and V_R is the reverse-breakdown voltage. The total overtemperature tolerance for the different grades follows:
 - a. C-grade: ±1.15% = ±0.5% ±100 ppm/°C × 65°C

b. D-grade: ±1.98% = ±1.0% ±150 ppm/°C × 65°C

Example: The C-grade LM4040-2.5 has an overtemperature Reverse-Breakdown Voltage tolerance of $\pm 2.5 \times 1.15\% = \pm 29$ mV.

3: When V_{OUT} ≤ 1.6V, the LM4041-ADJ must operate at reduced I_R. This is caused by the series resistance of the die attach between the die (-) output and the package (-) output pin. See the Output Saturation curve in the Typical Performance Curves section.

LM4041-ADJ ELECTRICAL CHARACTERISTICS (Note 1) (CONTINUED)

Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions
Reverse-Breakdown Voltage Long-Term Stability	ΔV _R	_	120	_	ppm	t = 1000 hrs., T _A = +25°C ±0.1°C, I _R = 100 μA
LM4041D						
Reverse-Breakdown Voltage	V _R		1.233	_	V	I _R = 100 μA, V _{OUT} = 5V
Reverse-Breakdown Voltage			_	±12	mV	I _R = 100 μA, T _A = +25°C
Tolerance (Note 2)		—	—	±24	mV	I _R = 100 μA
Minimum Operating Current	I _{RMIN}		45	65	μA	T _A = +25°C
		_	—	70		_
Reference Voltage Change with Operating Current	$\Delta V_{REF}/\Delta I_R$	_	0.7	2.0	mV	$\begin{split} _{\text{RMIN}} &\leq _{\text{R}} \leq 1 \text{ mA}, \\ \text{V}_{\text{OUT}} &\geq 1.6 \text{V} \text{ (Note 3)}, \\ \text{T}_{\text{A}} &= +25^{\circ}\text{C} \end{split}$
		—	—	2.5		I _{RMIN} ≤ I _R ≤ 1 mA, V _{OUT} ≥ 1.6V (Note 3)
		_	2.0	6.0		1 mA ≤ I _R ≤ 12 mA, V _{OUT} ≥ 1.6V (Note 3), T _A = +25°C
		—	—	8.0		1 mA ≤ I _R ≤ 12 mA, V _{OUT} ≥ 1.6V (Note 3)
Reference Voltage Change	$\Delta V_{REF} / \Delta V_O$	_	-1.55	-2.5	mV/V	I _R = 1 mA, T _A = +25°C
with Output Voltage Change		_	—	-3.0		I _R = 1 mA
Feedback Current	I _{FB}	_	60	150	nA	T _A = +25°C
			_	200		—
Average Reference Voltage Temperature Coefficient	ΔV _{REF} / ΔT	—	±20	—	ppm/°C	V _{OUT} = 5V, I _R = 10 mA, T _A = +25°C
			±15	±150		V _{OUT} = 5V, I _R = 1 mA
			±15	_		V_{OUT} = 5V, I _R = 100 µA, T _A = +25°C
Dynamic Output Impedance	Z _{OUT}	_	0.3	_	Ω	I _R = 1 mA, f = 120 Hz, T _A = +25°C, I _{AC} = 0.1 I _R , V _{OUT} = V _{REF}
			_	2.0	1	V _{OUT} = 10V, T _A = +25°C

 T_A = Operating Temperature Range, T_A = T_J = -40°C to +85°C, unless noted.

Note 1: Specification for packaged product only.

- 2: The boldface (overtemperature) limit for Reverse-Breakdown Voltage Tolerance is defined as the room temperature Reverse-Breakdown Voltage Tolerance $\pm [(\Delta V_R/\Delta T)(65^\circ C)(V_R)]$. $\Delta V_R/\Delta T$ is the V_R temperature coefficient, 65°C is the temperature range from -40°C to the reference point of 25°C, and V_R is the reverse-breakdown voltage. The total overtemperature tolerance for the different grades follows:
 - a. C-grade: ±1.15% = ±0.5% ±100 ppm/°C × 65°C
 - b. D-grade: ±1.98% = ±1.0% ±150 ppm/°C × 65°C

Example: The C-grade LM4040-2.5 has an overtemperature Reverse-Breakdown Voltage tolerance of $\pm 2.5 \times 1.15\% = \pm 29$ mV.

3: When V_{OUT} ≤ 1.6V, the LM4041-ADJ must operate at reduced I_R. This is caused by the series resistance of the die attach between the die (-) output and the package (-) output pin. See the Output Saturation curve in the Typical Performance Curves section.

LM4041-ADJ ELECTRICAL CHARACTERISTICS (Note 1) (CONTINUED)

T۸	= Operating	Temperature	Range, T	_^ = T	$_{\rm J}$ = -40°C to +85°C, unless noted.
• A	oporating	romporataro	riange, i	A '	

Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions
Wideband Noise	e _N		20		μV _{RMS}	I _R = 100 μA, T _A = +25°C, 10 Hz ≤ f ≤ 10 kHz
Reverse-Breakdown Voltage Long-Term Stability	ΔV _R		120			t = 1000 hrs., T _A = +25°C ±0.1°C, I _R = 100 μA

Note 1: Specification for packaged product only.

- 2: The boldface (overtemperature) limit for Reverse-Breakdown Voltage Tolerance is defined as the room temperature Reverse-Breakdown Voltage Tolerance ±[(ΔV_R/ΔT)(65°C)(V_R)]. ΔV_R/ΔT is the V_R temperature coefficient, 65°C is the temperature range from –40°C to the reference point of 25°C, and V_R is the reverse-breakdown voltage. The total overtemperature tolerance for the different grades follows:
 - a. C-grade: ±1.15% = ±0.5% ±100 ppm/°C × 65°C b. D-grade: ±1.98% = ±1.0% ±150 ppm/°C × 65°C

Example: The C-grade LM4040-2.5 has an overtemperature Reverse-Breakdown Voltage tolerance of $\pm 2.5 \times 1.15\% = \pm 29$ mV.

3: When V_{OUT} ≤ 1.6V, the LM4041-ADJ must operate at reduced I_R. This is caused by the series resistance of the die attach between the die (-) output and the package (-) output pin. See the Output Saturation curve in the Typical Performance Curves section.

TEMPERATURE SPECIFICATIONS (Note 1)

Sym.	Min.	Тур.	Max.	Units	Conditions			
T _A	-40	_	+85	°C	—			
Τ _S	-65	_	+150	°C	—			
_	—	+215	_	°C	Vapor phase, 60s			
_	—	+220		°C	Infrared, 15s			
Package Thermal Resistance								
Θ _{JA}	_	+326		°C/W	—			
	T _A T _S —	T _A -40 T _S -65 	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			

Note 1: The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature and the thermal resistance from junction to air (i.e., T_A, T_J, θ_{JA}). Exceeding the maximum allowable power dissipation will cause the device operating junction temperature to exceed the maximum +125°C rating. Sustained junction temperatures above +125°C can impact the device reliability.

Test Circuits

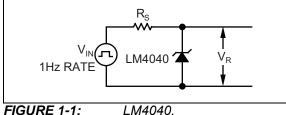
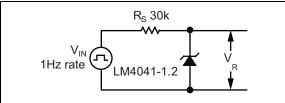
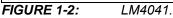


FIGURE 1-1:





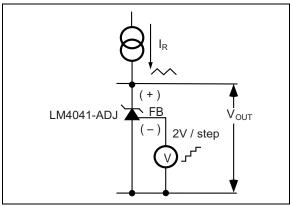


FIGURE 1-3: Test Circuit.

Reverse Characteristics

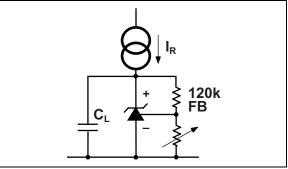


FIGURE 1-4: Output Impedance vs. Frequency Test Circuit.

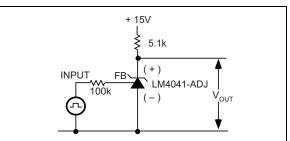


FIGURE 1-5: Large Signal Response Test Circuit.

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

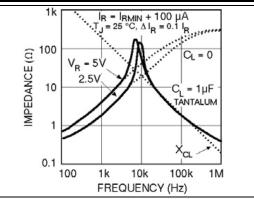


FIGURE 2-1: LM4040 Output Impedance vs. Frequency.

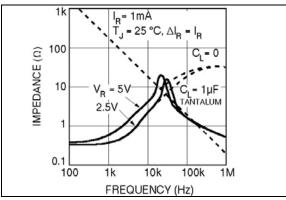


FIGURE 2-2: LM4040 Output Impedance vs. Frequency.

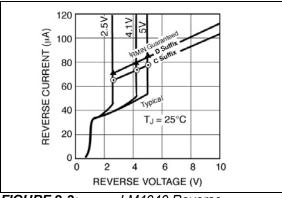


FIGURE 2-3: LM4040 Reverse Characteristics and Minimum Operating Current.

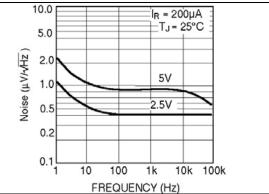


FIGURE 2-4: LM4040 Noise Voltage vs. Frequency.

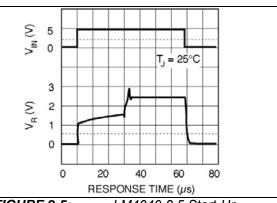
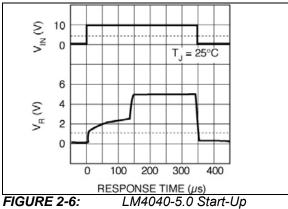


FIGURE 2-5: LM4040-2.5 Start-Up Characteristics ($R_S = 30 \ k\Omega$).



Characteristics ($R_S = 30 \ k\Omega$).

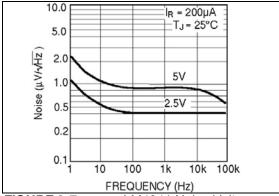
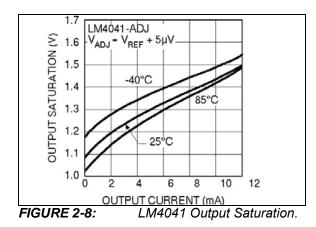


FIGURE 2-7: LM4041 Noise Voltage vs. Frequency.



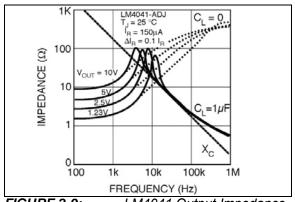


FIGURE 2-9:LM4041 Output Impedancevs. Frequency.

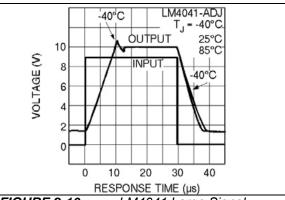


FIGURE 2-10: LM4041 Large Signal Response.

3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

TABLE 3-1:	PIN FUNCTION	IADLE				
Pin Number Fixed	Pin Number Adjustable	Pin Name Description				
1	2	+	Cathode. Connect to positive voltage.			
_	1	FB	Feedback. Connect to a resistive divider network to set the output voltage.			
2	3	-	Anode. Connect to negative voltage.			
3		NC	Not internally connected. This pin must be left floating or con- nected to –.			

TABLE 3-1: PIN FUNCTION TABLE

4.0 APPLICATION INFORMATION

The stable operation of the LM4040 and LM4041 references require an external capacitor greater than 10 nF connected between the (+) and (–) pins. Bypass capacitors with values between 100 pF and 10 nF have been found to cause the devices to exhibit instabilities.

4.1 Schottky Diode

LM4040-x.x and LM4041-1.2 in the SOT-23 package have a parasitic Schottky diode between Pin 2 (–) and Pin 3 (die attach interface connect). Pin 3 of the SOT-23 package must float or be connected to Pin 2. The LM4041-ADJ use Pin 3 as the (–) output.

4.2 Conventional Shunt Regulator

In a conventional shunt regulator application (see Figure 5-1), an external series resistor (R_S) is connected between the supply voltage and the LM4040-x.x or LM4041-1.2 reference. R_S determines the current that flows through the load (I_1) and the reference (I_O). Because load current and supply voltage may vary, R_S should be small enough to supply at least the minimum acceptable I_{Q} to the reference even when the supply voltage is at its minimum and the load current is at its maximum value. When the supply voltage is at its maximum and I_{I} is at its minimum, R_{S} should be large enough so that the current flowing through the LM4040-x.x is less than 15 mA, and the current flowing through the LM4041-1.2 or LM4041-ADJ is less than 12 mA.

 R_S is determined by the supply voltage (V_S), the load and operating current, (I_L and I_Q), and the reference's reverse breakdown voltage (V_R):

EQUATION 4-1:

$$R_S = \frac{(V_S - V_R)}{(I_L + I_Q)}$$

4.3 Adjustable Regulator

The LM4041-ADJ's output voltage can be adjusted to any value between 1.24V and 10V. It is a function of the internal reference voltage (V_{REF}) and the ratio of the external feedback resistors as shown in Figure 5-2. The output is found using the following equation:

EQUATION 4-2:

 $V_{O} = V_{REF}[(R2/R1) + 1]$

Where:

V_O Desired Output Voltage

The actual value of the internal V_{REF} is a function of $V_O.$ The corrected V_{REF} is determined by:

 $V_{REF} = V_O \times \left(\frac{\Delta V_{REF}}{\Delta V_O}\right) + V_Y$

EQUATION 4-3:

Where:

V_O Desired Output Voltage

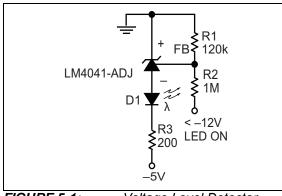
 $\Delta V_{REF}/\Delta V_O$ is found in the Electrical Characteristics section and is typically –1.3 mV/V and V_Y is equal to 1.233V. Replace the value of V_{REF} in Equation 4-2 with the value V_{REF} found using Equation 4-3.

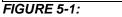
Note that actual output voltage can deviate from that predicted using the typical $\Delta V_{REF}/\Delta V_O$ in Equation 4-3; for C-grade parts, the worst case $\Delta V_{REF}/\Delta V_O$ is – 2.5 mV/V and V_Y = 1.248V.

The following example shows the difference in output voltage resulting from the typical and worst case values of $\Delta V_{REF}/\Delta V_O.$

Let V_O = +9V. Using the typical values of $\Delta V_{REF}/\Delta V_{O}$, V_{REF} is 1.223V. Choosing a value of R1 = 10 k Ω , R2 = 63.272 k Ω . Using the worst case $\Delta V_{REF}/\Delta V_O$ for the C-grade and D-grade parts, the output voltage is actually 8.965V and 8.946V respectively. This results in possible errors as large as 0.39% for the C-grade parts and 0.59% for the D-grade parts. Once again, resistor values found using the typical value of $\Delta V_{REF}/\Delta V_O$ will work in most cases, requiring no further adjustment.

5.0 TYPICAL APPLICATION CIRCUITS





Voltage Level Detector.

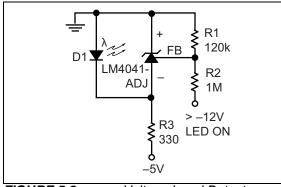
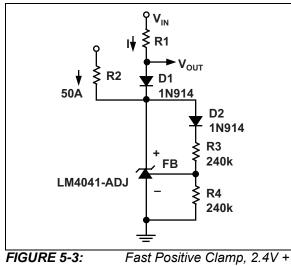


FIGURE 5-2: Voltage Level Detector.



 ΔV_{D1} .

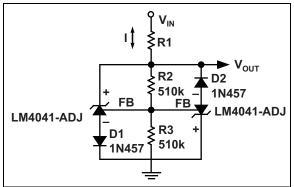
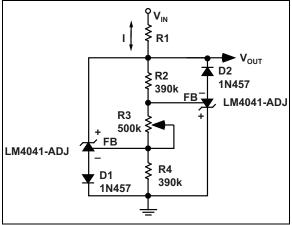
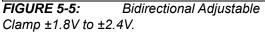


FIGURE 5-4: Bidirectional Clamp ±2.4V.





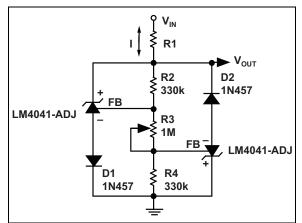
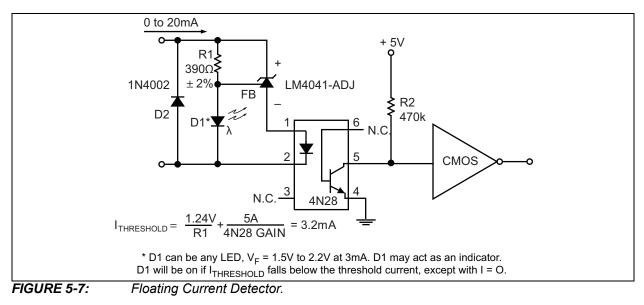
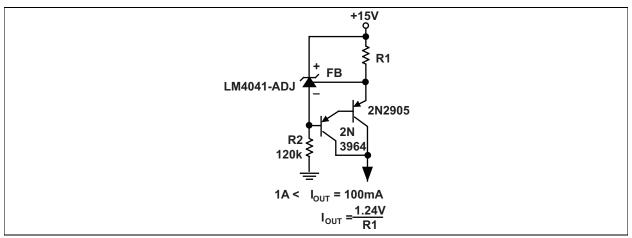
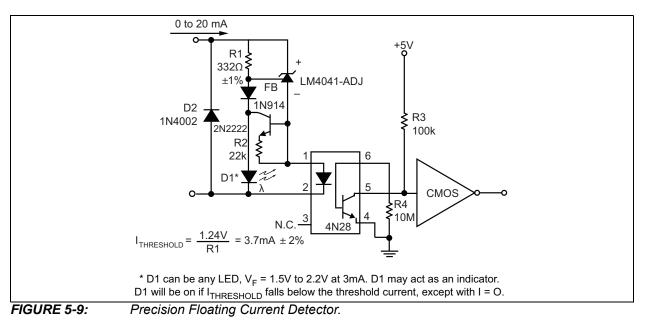


FIGURE 5-6: Bidirectional Adjustable Clamp ±2.4V to ±6V.



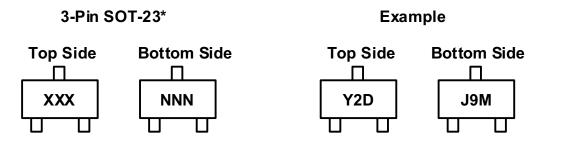






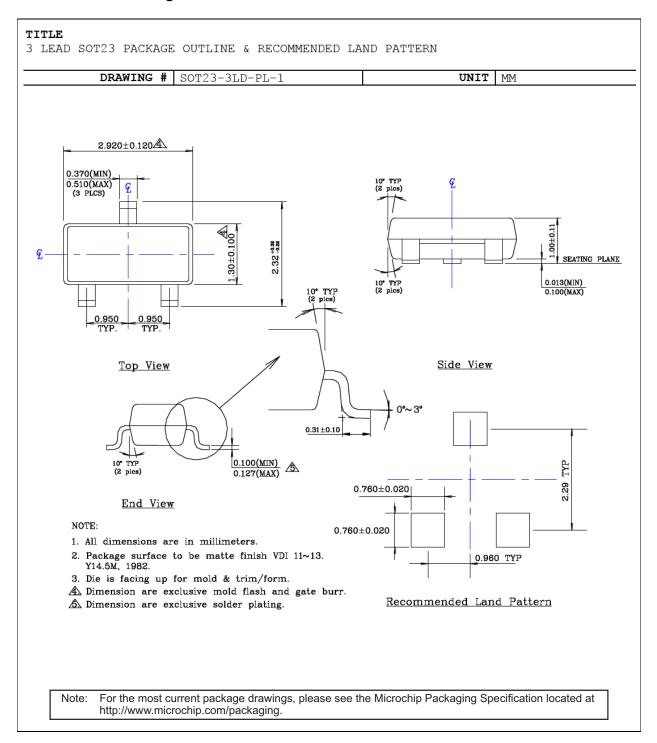
6.0 PACKAGING INFORMATION

6.1 Package Marking Information



Device	Top Side Marking
LM4040CYM3-2.5-TR	Y2C
LM4040CYM3-4.1-TR	Y4C
LM4040CYM3-5.0-TR	Y5C
LM4040DYM3-2.5-TR	Y2D
LM4040DYM3-4.1-TR	Y4D
LM4040DYM3-5.0-TR	Y5D
LM4041CYM3-ADJ-TR	YAC
LM4041CYM3-1.2-TR	Y1C
LM4041DYM3-ADJ-TR	YAD
LM4041DYM3-1.2-TR	Y1D

Legend	: XXX Y YY WW NNN (€3) * •, ▲, ▼ mark).	Product code or customer-specific information Year code (last digit of calendar year) Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code Pb-free JEDEC [®] designator for Matte Tin (Sn) This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.
	be carried characters the corpor	nt the full Microchip part number cannot be marked on one line, it will d over to the next line, thus limiting the number of available for customer-specific information. Package may or may not include ate logo. (_) and/or Overbar (⁻) symbol may not be to scale.



3-Lead SOT-23 Package Outline and Recommended Land Pattern

APPENDIX A: REVISION HISTORY

Revision A (April 2017)

- Converted Micrel data sheet LM4040/LM4041 to Microchip DS20005757A.
- Minor text changes throughout.
- Updated temperature information in all Electrical Characteristics tables to better reflect which values are valid for $T_A = +25^{\circ}C$.

Revision B (July 2018)

- Corrected part number for Reverse Current in Operating Ratings ‡ to LM4041-ADJ.
- Updated Section 6.1 "Package Marking Information" drawing and information.
- Updated information in Product Identification System.
- Updated "Reverse-Breakdown Voltage Change with Operating Current Change" conditions for LM4041-1.2 Electrical Characteristics (Note 1) and LM4041-ADJ Electrical Characteristics (Note 1).

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

PART NO. X	(X	xx	<u>-X.X</u>	-XX	Example	es:	
Device Accur Temper Coeffi	racy, Tem rature _R	Т			Media Type	a) LM404	0CYM3-2.5-TR:	LM4040, ±0.5%, 100 ppm/°C, -40°C to +85°C Temp. Range 3-Lead SOT-23, 2.500V, 3,000/Reel
Device:	LM4040: LM4041:	Refer	ence sion Micropov	wer Shunt Vo wer Shunt Vo	•	b) LM404	0CYM3-4.1-TR:	LM4040, ±0.5%, 100 ppm/°C, -40°C to +85°C Temp. Range 3-Lead SOT-23, 4.096V, 3,000/Reel
Accuracy, Temp. Coefficient:	C = D =		100 ppm/°C 150 ppm/°C			c) LM404	0CYM3-5.0-TR:	LM4040, ±0.5%, 100 ppm/°C, -40°C to +85°C Temp. Range 3-Lead SOT-23, 5.000V, 3,000/Reel
Temperature Range:	Y =		to +85°C (Inc	dustrial)		d) LM404	0DYM3-2.5-TR:	LM4040, ±1.0%, 150 ppm/°C, -40°C to +85°C Temp. Range 3-Lead SOT-23, 2.500V, 3,000/Reel
Package: Voltage:	M3 = -2.5 -4.1 -5.0	3-Lead = 2.500 = 4.096 = 5.000	6V			e) LM404	0DYM3-4.1-TR:	LM4040, ±1.0%, 150 ppm/°C, -40°C to +85°C Temp. Range 3-Lead SOT-23, 4.096V, 3,000/Reel
Media Type	-3.0 -1.2 ADJ TR	= 1.225 = 1.24	5V (LM4041 (/ to 10V (LM-)/Reel			f) LM4040	DYM3-5.0-TR:	LM4040, ±1.0%, 150 ppm/°C, -40°C to +85°C Temp. Range 3-Lead SOT-23, 5.000V, 3,000/Reel
		- 0,000				g) LM404	1CYM3-ADJ-TR:	LM4041, ±0.5%, 100 ppm/°C, -40°C to +85°C Temp. Range 3-Lead SOT-23, 1.24V to 10V, 3,000/Reel
						h) LM404	1CYM3-1.2-TR:	LM4041, ±0.5%, 100 ppm/°C, -40°C to +85°C Temp. Range 3-Lead SOT-23, 1.225V, 3,000/Reel
						i) LM4041	IDYM3-ADJ-TR:	LM4041, ±1.0%, 150 ppm/°C, -40°C to +85°C Temp. Range 3-Lead SOT-23, 1.24V to 10V, 3,000/Reel
						j) LM4041	IDYM3-1.2-TR:	LM4041, ±1.0%, 150 ppm/°C, -40°C to +85°C Temp. Range 3-Lead SOT-23, 1.225V, 3,000/Reel
						Note 1:	catalog part numb used for ordering the device packag	entifier only appears in the ber description. This identifier is purposes and is not printed on ge. Check with your Microchip ackage availability with the tion.

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- · Microchip products meet the specification contained in their particular Microchip Data Sheet.
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